wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

2. (Amended) A device according to claim 1, wherein a thickness of the tungsten nitride film is 10 to 50 nm and a thickness of the tungsten film is 200 to 400 nm.

3. (Twice Amended) A device according to claim 1, wherein electrical resistivity of the wiring is equal to or less than 40 μΩcm.

4. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wirings comprising a metal film and a nitride film of the metal film, the metal film located on the nitride film,

wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

5. (Twice Amended) A device according to claim 4, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

6. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

7. (Twice Amended) A device according to claim 4, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

9. (Twice Amended) A device according to claim 4, wherein internal stress of the wiring is from $-1 \times 10^{10}$ dyn/cm$^2$ to $+1 \times 10^{10}$ dyn/cm$^2$.

10. (Twice Amended) A device according to claim 4, wherein line width of the wiring is equal to or less than 5 μm.

11. (Twice Amended) A device according to claim 4, wherein film thickness of the wiring is equal to or greater than 0.1 μm, and equal to or less than 0.7 μm.

12. (Twice Amended) A device according to claim 4, wherein the wiring is used as a gate electrode of a TFT.

13. (Twice Amended) A device according to claim 4, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω.

16. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wiring comprising a tungsten nitride film and a tungsten film formed thereon; and

an insulating film formed over the wiring, said insulating film comprising SiOxNy,

wherein the wiring includes at least one inert element and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

17. (Twice Amended) A device according to claim 16, further comprising a semiconductor film adjacent to the wiring with an insulating film interposed therebetween.

18. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 1 atom%.

19. (Twice Amended) A device according to claim 16, wherein the inert element except for argon is contained within the wiring at an amount equal to or less than 0.1 atom%.

21. (Twice Amended) A device according to claim 16, wherein internal stress of the tungsten film or of the wiring is from $-1 \times 10^{10}$ dyn/cm$^2$ to $+1 \times 10^{10}$ dyn/cm$^2$.

22. (Twice Amended) A device according to claim 16, wherein line width of the wiring is equal to or less than 5 μm.

23. (Twice Amended) A device according to claim , wherein film thickness of the wiring is equal to or greater than 0.1 μm, and equal to or less than 0.7 μm.

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24. (Twice Amended) A device according to claim 16, wherein the wiring is used as a gate electrode of a TFT.

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25. (Twice Amended) A device according to claim 16, wherein resistance value per 1 square μm of surface area of a connection between the wiring and an aluminum wiring is equal to or less than 40 Ω.

28. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate having a lamination structure comprising a phosphorus doped silicon, a nitride film of tungsten, and a film comprising tungsten,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon, and

wherein an amount of sodium contained within the wiring is equal to or less than 0.3 ppm.

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36. (Amended) A device according to claim 28, wherein the wiring is used as a gate electrode of a TFT.

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40. (Twice Amended) A semiconductor device comprising:

a wiring formed over a substrate, the wiring having a lamination structure containing a tungsten nitride film and a film comprising tungsten formed thereon,

wherein the film comprising tungsten includes at least one inert element, and 90% or more of the inert element is argon,

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